PROCESS CP312

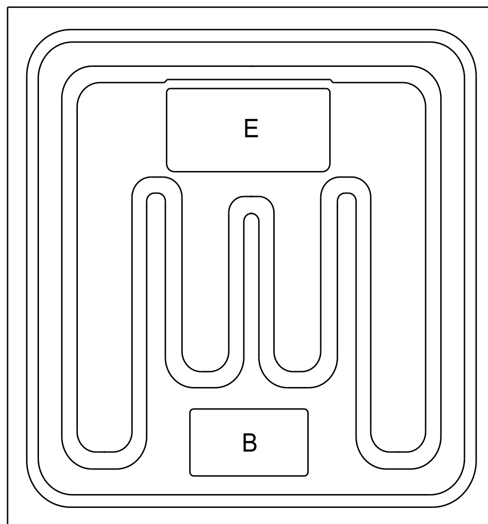
Power Transistor

NPN - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	70 x 70 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	11.4 x 18.1 MILS
Emitter Bonding Pad Area	13.8 x 23.6 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ti/Ni/Ag - 11,300Å

GEOMETRY



BACKSIDE COLLECTOR R1

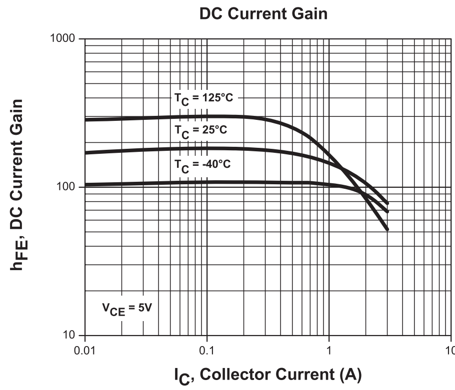
GROSS DIE PER 4 INCH WAFER
2,230

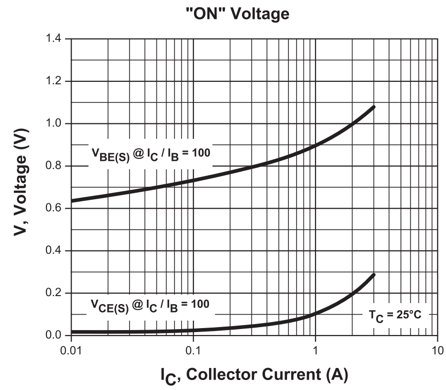
PRINCIPAL DEVICE TYPES
CZT3120

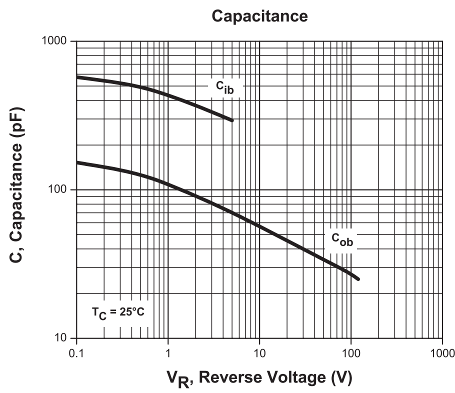
R4 (22-March 2010)

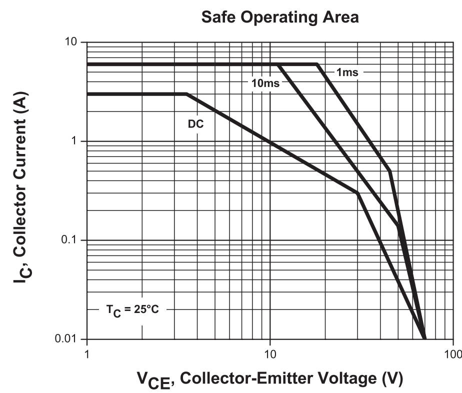
PROCESS CP312

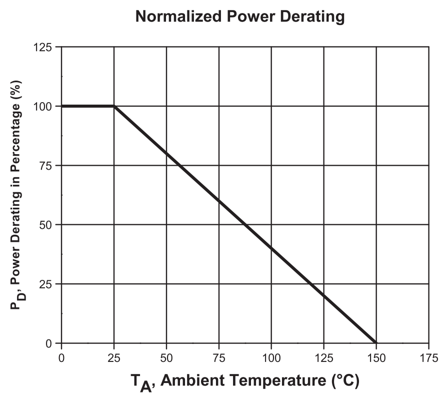
Typical Electrical Characteristics

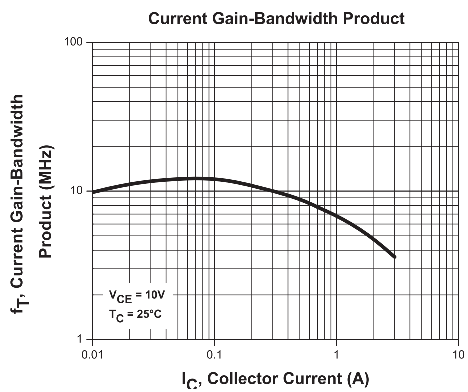












R4 (22-March 2010)